

Corrigendum

Naphthalene diimide-based polymeric semiconductors. Effect of chlorine incorporation and n-channel transistors operating in water – CORRIGENDUM

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In Ryu et al.,¹ there should have been an additional author, Simone Fabiano, included in the author list. Therefore, the updated author list is as follows:

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The authors regret this omission.

Reference

1. G.-S. Ryu, Z. Chen, S. Fabiano, H. Usta, Y.-Y. Noh, and A. Facchetti: Naphthalene diimide-based polymeric semiconductors. Effect of chlorine incorporation and n-channel transistors operating in water. *MRS Communications* **6**, 47–60 (2016). doi: 10.1557/mrc.2016.4.